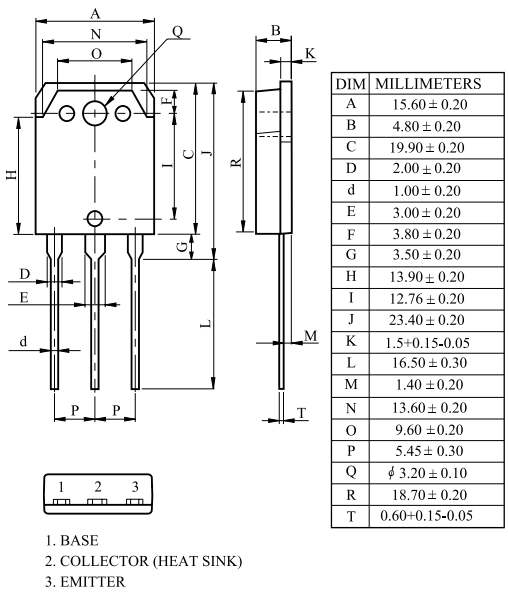
KTB817B

TRIPLE DIFFUSED PNP TRANSISTOR

HIGH POWER AMPLIFIER APPLICATION.

FEATURES

- Complementary to KTD1047B.
- Recommended for 60W Audio Frequency Amplifier Output Stage.



DIM	MILLIMETERS
A	15.60 ± 0.20
B	4.80 ± 0.20
C	19.90 ± 0.20
D	2.00 ± 0.20
d	1.00 ± 0.20
E	3.00 ± 0.20
F	3.80 ± 0.20
G	3.50 ± 0.20
H	13.90 ± 0.20
I	12.76 ± 0.20
J	23.40 ± 0.20
K	1.5+0.15-0.05
L	16.50 ± 0.30
M	1.40 ± 0.20
N	13.60 ± 0.20
O	9.60 ± 0.20
P	5.45 ± 0.30
Q	ϕ 3.20 ± 0.10
R	18.70 ± 0.20
T	0.60+0.15-0.05

TO-3P(N)-E

MAXIMUM RATING (Ta=25℃)

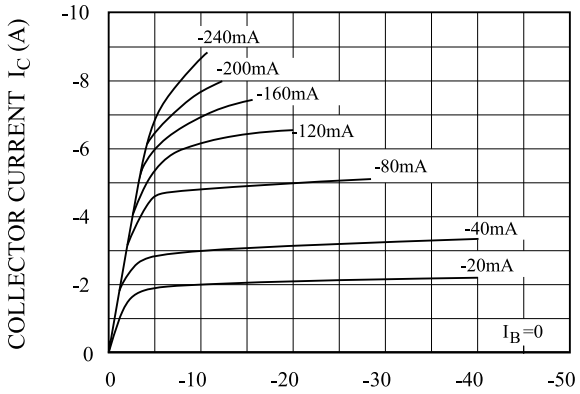
CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	-160	V
Collector-Emitter Voltage		V_{CEO}	-140	V
Emitter-Base Voltage		V_{EBO}	-6	V
Collector Current	DC	I_C	-12	A
	Pulse	I_{CP}	-15	
Collector Power Dissipation (Tc=25℃)		P_C	100	W
Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	-55 150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

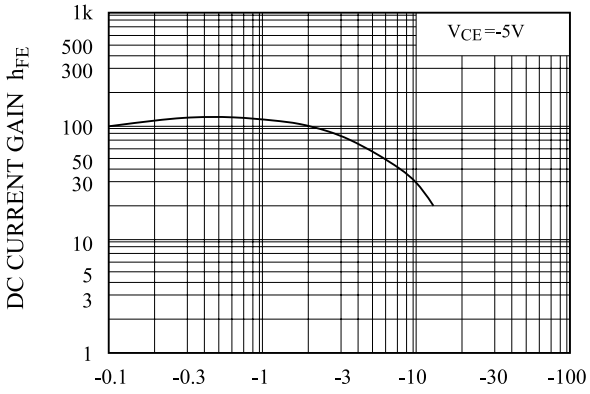
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=-80V, I_E=0	-	-	-0.1	mA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-4V, I_C=0	-	-	-0.1	mA
DC Current Gain	h_{FE} (1) (Note)	V_{CE}=-5V, I_C=-1A	60	-	200	
	h_{FE} 2	V_{CE}=-5V, I_C=-6A	20	-		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-5A, I_B=-0.5A	-	-	-2.5	V
Base-Emitter Voltage	V_{BE}	V_{CE}=-5V, I_C=-1A	-	-	-1.5	V
Transition Frequency	f_T	V_{CE}=-5V, I_C=-1A	-	15	-	MHz
Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz	-	300	-	pF
Turn On Time	t_{on}	V_{CC}=-20V I_C=1A=10 · I_{B1}=-10 · I_{B2} R_L=20Ω	-	0.25	-	μS
Fall Time	t_f		-	0.53	-	
Storage Time	t_{stg}		-	1.61	-	

Note : h_{FE}(1) Classification O:60 120, Y:100 200

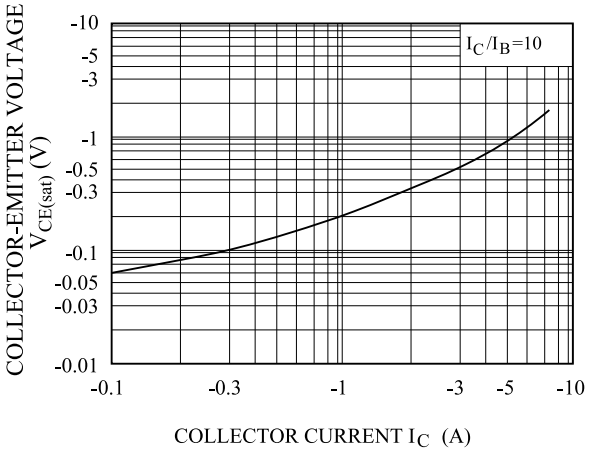
I_C - V_{CE}



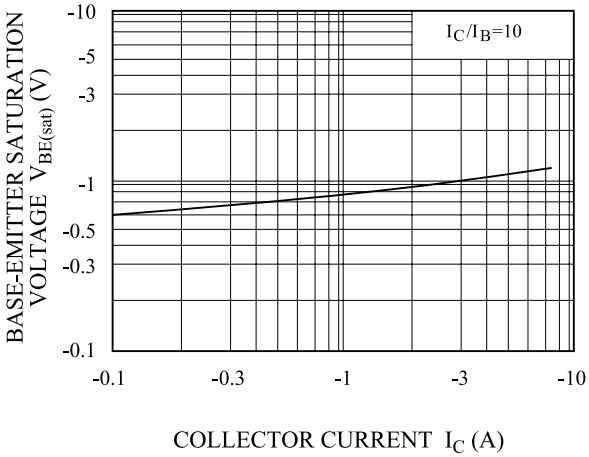
h_{FE} - I_C



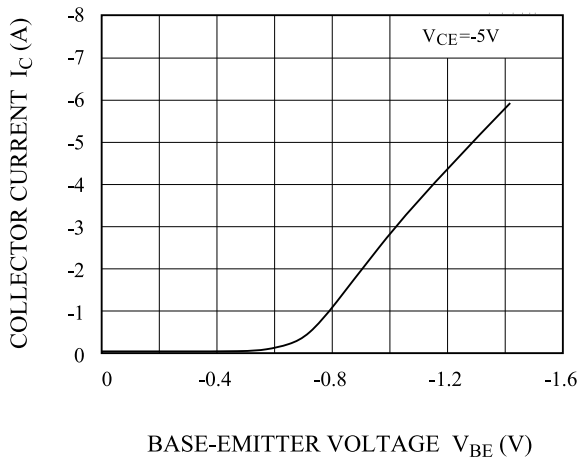
$V_{CE(sat)}$ - I_C



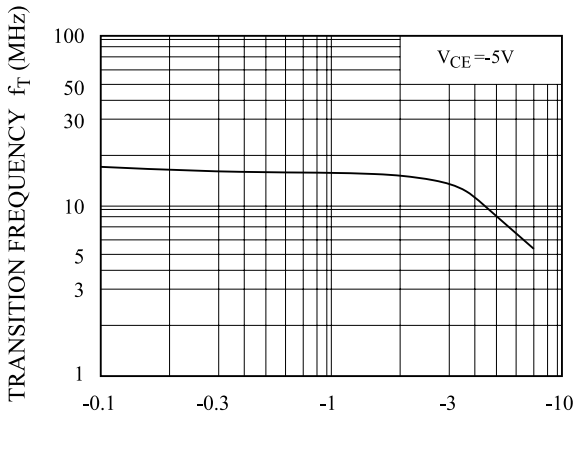
$V_{BE(sat)}$ - I_C



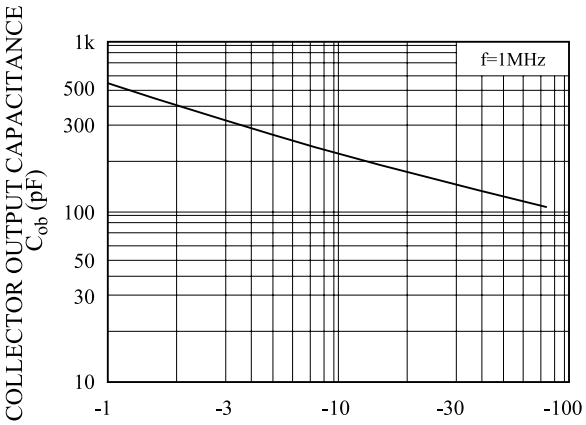
I_C - V_{BE}



f_T - I_C



C_{ob} - V_{CB}



SAFE OPERATING AREA

